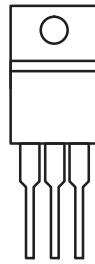
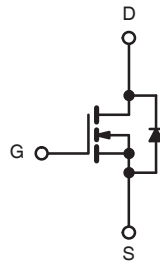


N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A) ^a	Q_g (Typ.)
30	0.0065 at $V_{GS} = 10$ V	60	32 nC
	0.0078 at $V_{GS} = 4.5$ V		

TO-220AB

 G D S
 Top View


N-Channel MOSFET

FEATURES

- DT-Trench Power MOSFET
- 100 % R_g Tested
- 100 % Avalanche Tested

APPLICATIONS

- Low-Side Switch for DC/DC Converters
 - Servers
 - POL
 - VRM
- OR-ing


RoHS
 COMPLIANT

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ($T_J = 150$ °C)	I_D	$T_C = 25$ °C 60 ^a	A
		$T_C = 70$ °C 55 ^{b,c}	
		$T_A = 25$ °C 30 ^{b, c}	
		$T_A = 70$ °C 26 ^{b, c}	
Pulsed Drain Current	I_{DM}	180	
Continuous Source-Drain Diode Current	I_S	$T_C = 25$ °C 60 ^a	
		$T_A = 25$ °C 4.7 ^{b, c}	
Single Pulse Avalanche Current	I_{AS}	55	mJ
Single Pulse Avalanche Energy	E_{AS}	130	
Maximum Power Dissipation	P_D	$T_C = 25$ °C 85	W
		$T_C = 70$ °C 55	
		$T_A = 25$ °C 5.7 ^{b, c}	
		$T_A = 70$ °C 3.8 ^{b, c}	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	°C
Soldering Recommendations (Peak Temperature)		260	

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient	R_{thJA}	17	25	°C/W
Maximum Junction-to-Case (Drain)	R_{thJC}	1.0	1.5	

Notes:

 a. Based on $T_C = 25$ °C.

b. Surface Mounted on 1" x 1" FR4 board.

 c. $t = 10$ s.

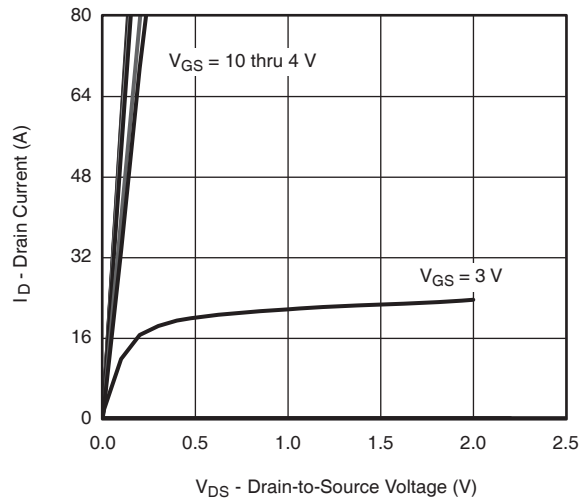
SPECIFICATIONS $T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted							
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	30			V	
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$		26		mV/ $^{\circ}\text{C}$	
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			- 6.5			
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1		3	V	
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$			1	μA	
		$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^{\circ}\text{C}$			10		
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	60			A	
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 20\text{ A}$		0.0065	0.0075	Ω	
		$V_{GS} = 4.5\text{ V}, I_D = 20\text{ A}$		0.0078	0.0089		
Forward Transconductance ^a	g_{fs}	$V_{DS} = 10\text{ V}, I_D = 20\text{ A}$		100		S	
Dynamic ^b							
Input Capacitance	C_{iss}	$V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		2890		pF	
Output Capacitance	C_{oss}			800			
Reverse Transfer Capacitance	C_{rss}			290			
Total Gate Charge	Q_g	$V_{DS} = 15\text{ V}, V_{GS} = 10\text{ V}, I_D = 20\text{ A}$		32	70	nC	
		$V_{DS} = 15\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 20\text{ A}$		22	40		
Gate-Source Charge	Q_{gs}			10			
Gate-Drain Charge	Q_{gd}			7			
Gate Resistance	R_g	$f = 1\text{ MHz}$		1.8		Ω	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\text{ V}, R_L = 1.5\text{ }\Omega$ $I_D \cong 10\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$		20		ns	
Rise Time	t_r			7			
Turn-Off Delay Time	$t_{d(off)}$			55			
Fall Time	t_f			11			
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 10\text{ V}, R_L = 1\text{ }\Omega$ $I_D \cong 10\text{ A}, V_{GEN} = 4.5\text{ V}, R_g = 1\text{ }\Omega$		49			
Rise Time	t_r			19			
Turn-Off Delay Time	$t_{d(off)}$			65			
Fall Time	t_f			32			
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I_S	$T_C = 25\text{ }^{\circ}\text{C}$			60		A
Pulse Diode Forward Current ^a	I_{SM}				180		
Body Diode Voltage	V_{SD}	$I_S = 4\text{ A}$		0.7	1.2	V	
Body Diode Reverse Recovery Time	t_{rr}	$I_F = 10\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^{\circ}\text{C}$		33	52	ns	
Body Diode Reverse Recovery Charge	Q_{rr}			22	45	nC	
Reverse Recovery Fall Time	t_a			17		ns	
Reverse Recovery Rise Time	t_b			19			

Notes:

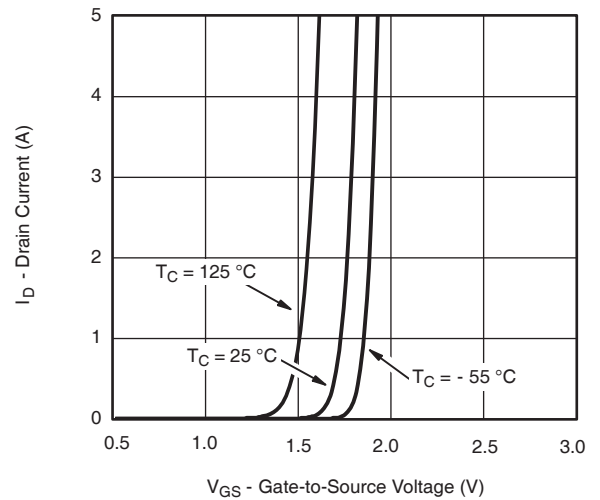
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
 b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

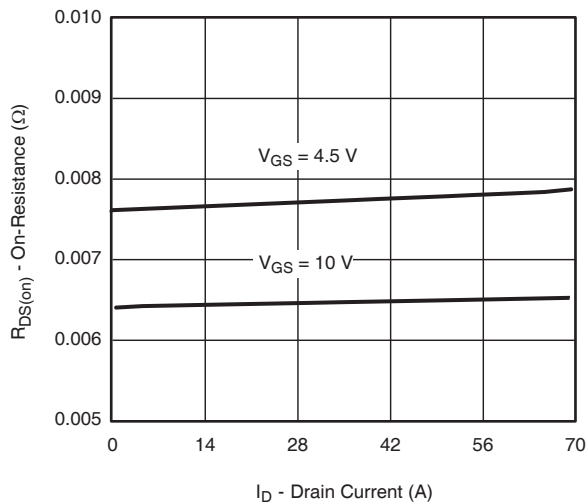
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



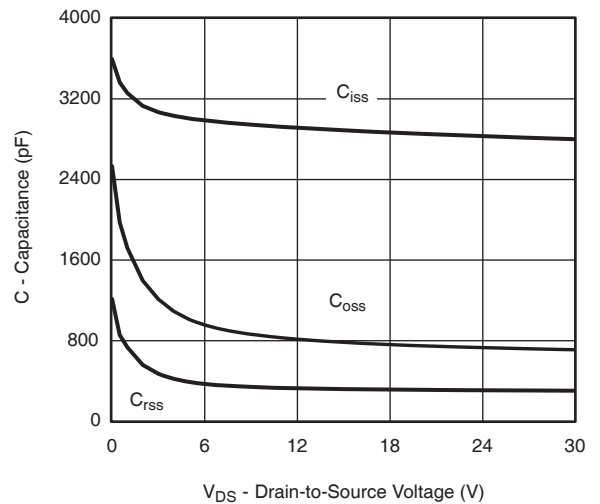
Output Characteristics



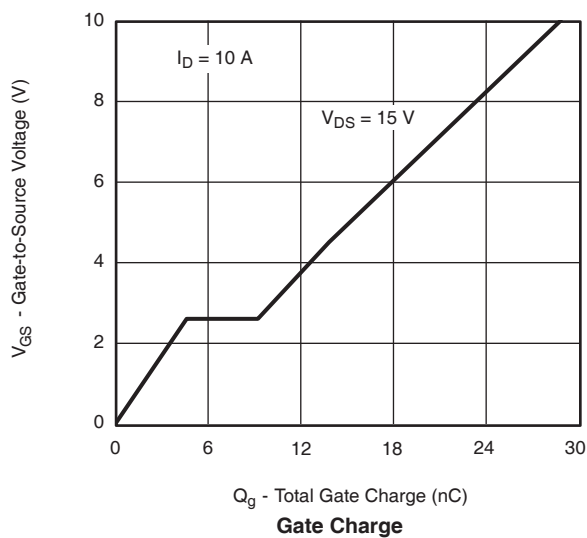
Transfer Characteristics



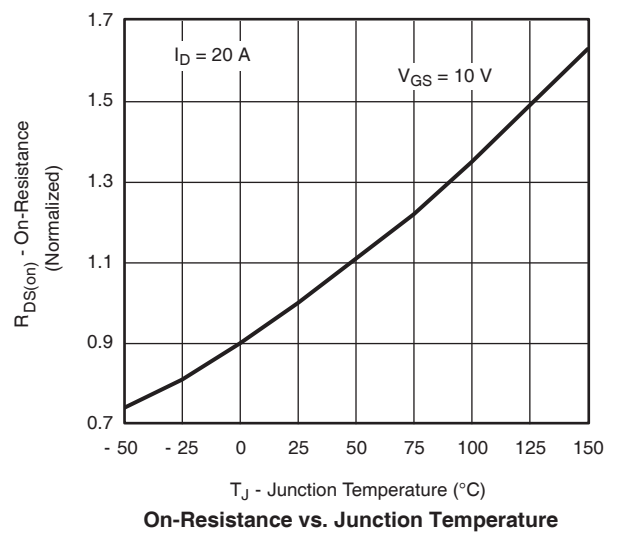
On-Resistance vs. Drain Current and Gate Voltage



Capacitance

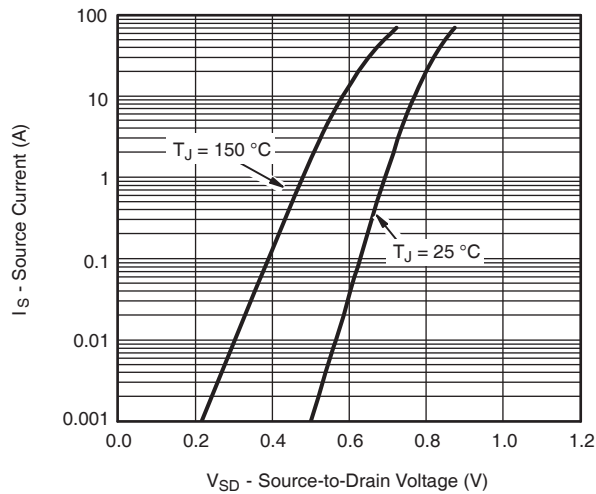


Gate Charge

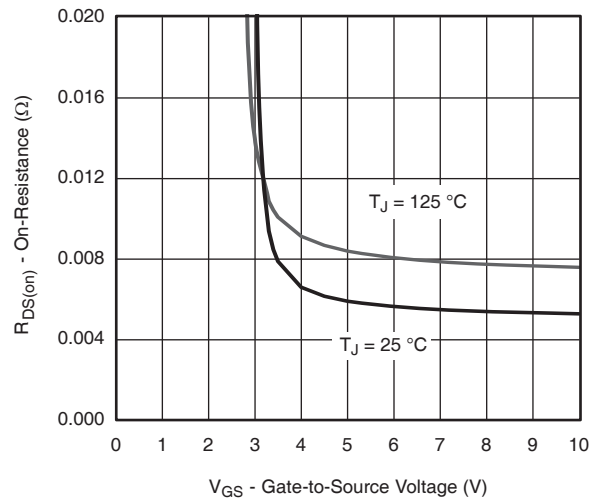


On-Resistance vs. Junction Temperature

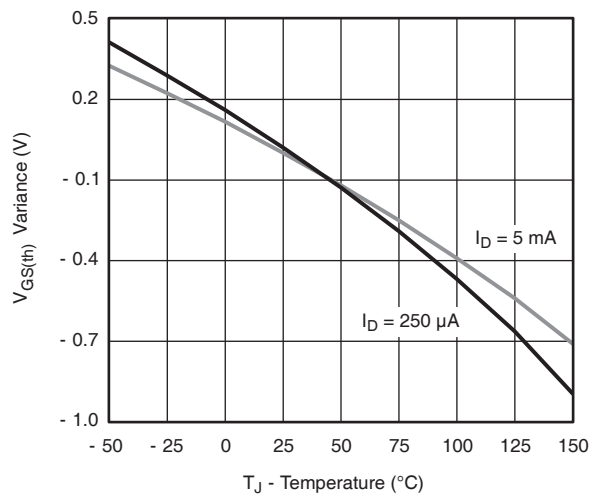
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



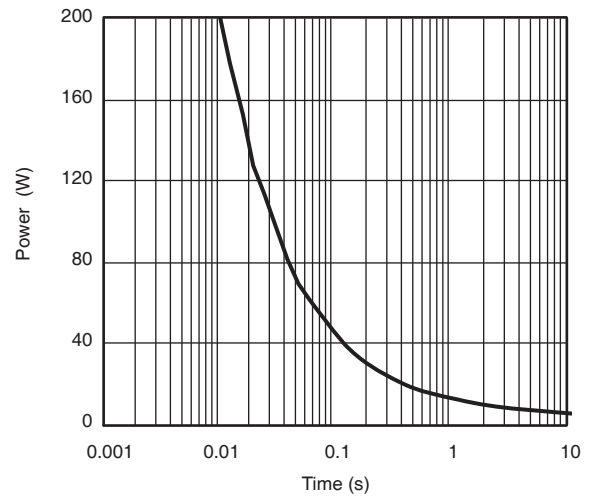
Source-Drain Diode Forward Voltage



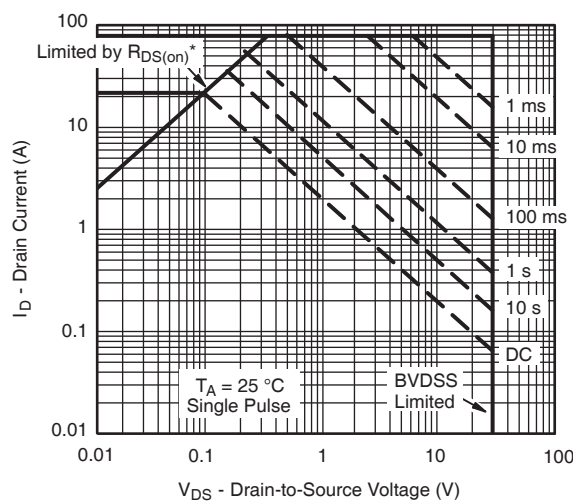
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



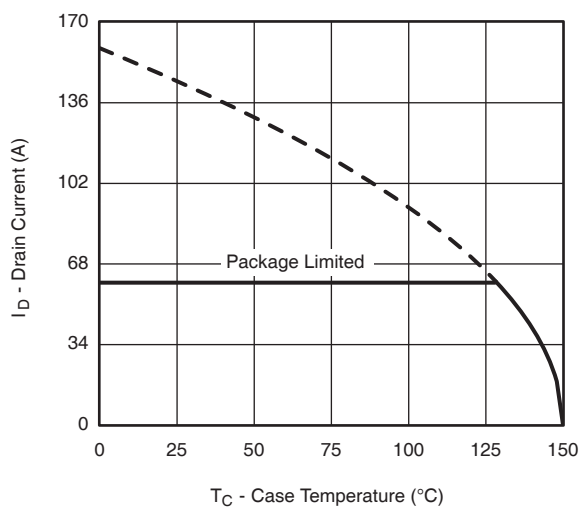
Single Pulse Power, Junction-to-Ambient



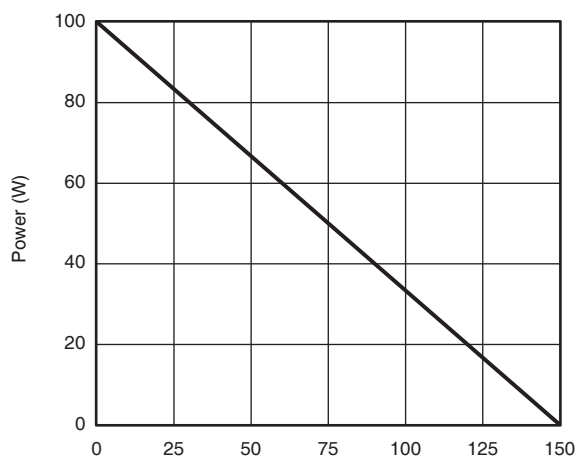
* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient

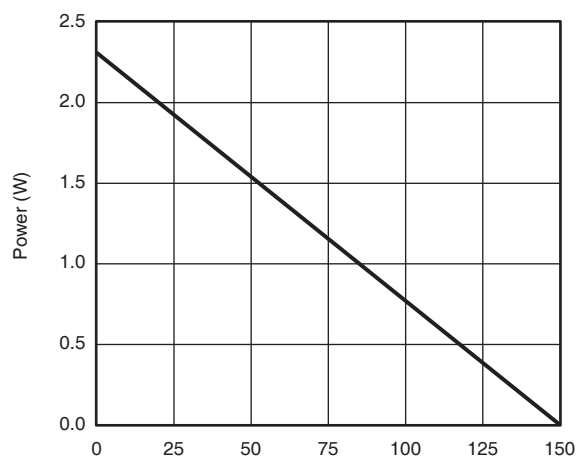
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Current Derating*



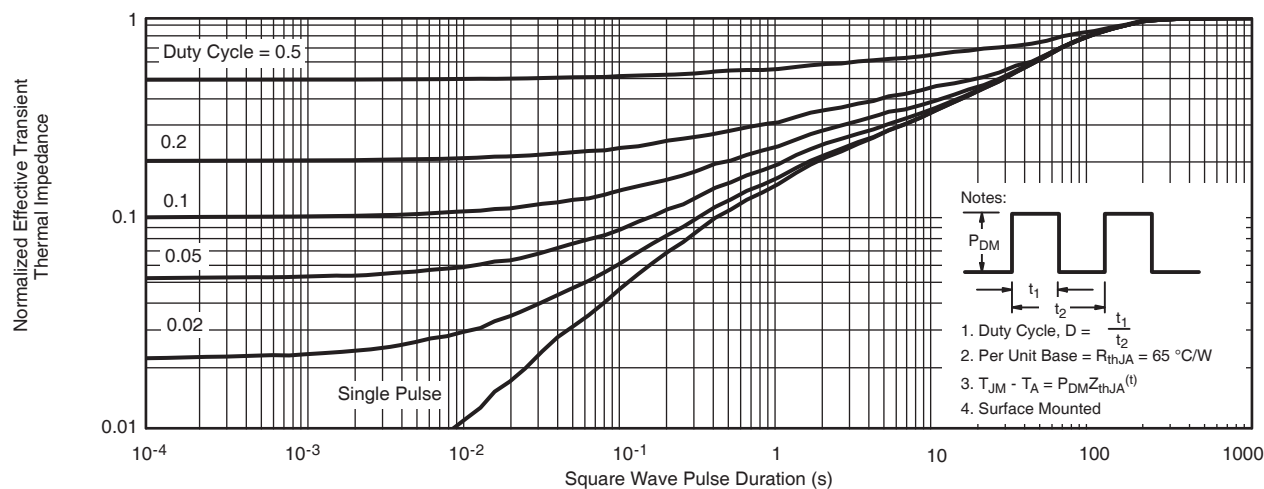
Power, Junction-to-Case



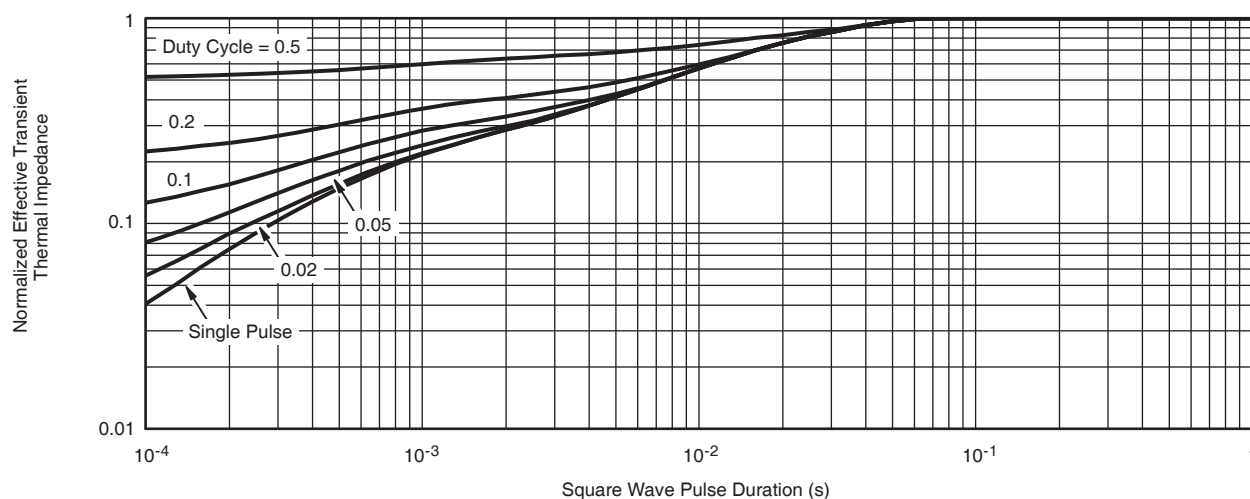
Power, Junction-to-Ambient

* The power dissipation P_D is based on $T_{J(max)} = 150\text{ }^{\circ}\text{C}$, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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